

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning on page 5, line 1, with the following amended paragraph:

Preferably, the mesh grid is formed of invar Invar®. Invar® is a commercially available low thermal expansion alloy consisting of Fe, Ni, Cr, Mn, Si, C, P, S and Co.

Please replace the paragraph beginning on page 5, line 19, with the following amended paragraph:

Preferably, the mesh grid is formed of invar Invar®.

Please replace the paragraph beginning on page 7, line 3, with the following amended paragraph:

A cathode electrode 120 is formed on a rear plate 110 of the cathode plate 100, and a gate insulation layer 130 is formed on the cathode electrode 120. A through hole 130a, through which the cathode electrode 120 is exposed, is formed in the gate insulation layer 130. An electron emission source 140, such as a carbon nano tube (CNT), is formed on the cathode electrode 120 exposed through the through hole 130a. A gate electrode 140 150 is formed on the gate insulation layer 130 to have a gate hole 150a corresponding to the through hole 130a.

Please replace the paragraph beginning on page 8, line 16, with the following amended paragraph:

As shown in FIG. 7, the spacers 300 are arranged on and then bonded to the anode plate 200. Here, the spacers 300 are bonded to the anode plate 200 by using paste-type binders 301 310. The fluorescent layer 230 is sintered and the binders 301 310 are hardened at the same time by heating a coupled body of the spacers 300 and the anode plate 200.

Please replace the paragraph beginning on page 8, line 25, with the following amended paragraph:

As described above, the mesh grid 400 is not installed between the cathode plate 100 and the anode plate 200 until the fluorescent material layer 230 and the binders 301 310 are sintered. Accordingly, it is possible to effectively prevent the mesh grid 400 from being deformed during the sintering of the fluorescent layer 230 and the binders 301 310.

Please replace the paragraph beginning on page 9, line 1, with the following amended paragraph:

As shown in FIG. 10, a SiO₂ paste is printed on an invar Invar® having a thickness of about 50 – 100 microns by squeezing the SiO₂ paste on the invar Invar® and then is sintered at a temperature of about 530 °C

Please replace the paragraph beginning on page 9, line 4, with the following amended paragraph:

As shown in FIG. 11, an electron control hole 420 is formed in the invar Invar® by photolithography. During the photolithography, a photoresist mask having a window corresponding to the electron control hole 420 can be used, and ferric chloride can be used as an etchant.

Please replace the paragraph beginning on page 9, line 8, with the following amended paragraph:

As shown in FIG. 12, the SiO₂ layer 440 is etched using the invar Invar® 400 having the electron control hole 420 as a mask so that the electron control hold 420 can be a through hole.